

Low-Voltage Dual SPST Analog Switch

DESCRIPTION

The DG9432, DG9433, DG9434 is a dual single-pole/single-throw monolithic CMOS analog switch designed for high performance switching of analog signals. Combining low power, high speed (t_{ON} : 25 ns, t_{OFF} : 20 ns), the DG9432, DG9433, DG9434 is ideal for portable and battery powered applications requiring high performance and efficient use of board space.

The DG9432, DG9433, DG9434 is built on Vishay Siliconix's low voltage BCD-15 process. An epitaxial layer prevents latchup. Break-before-make is guaranteed for DG9432, DG9433, DG9434.

Each switch conducts equally well in both directions when on, and blocks up to the power supply level when off.

FEATURES

- Wide operation voltage (+ 2.7 V to + 12 V)
- Low charge injection - Q_{INJ} : 1 pC
- Low power consumption
- TTL/CMOS logic compatible over the full operating voltage range
- Available in MSOP-8 and SOT23-8
- **Compliant to RoHS Directive 2002/95/EC**



RoHS
COMPLIANT

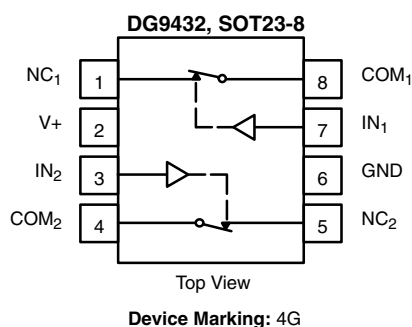
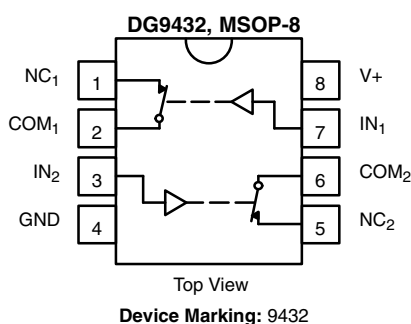
BENEFITS

- Reduced power consumption
- Simple logic interface
- High accuracy
- Reduce board space

APPLICATIONS

- Battery operated systems
- Portable test equipment
- Sample and hold circuits
- Cellular phones
- Communication systems
- Military radio
- PBX, PABX guidance and control systems

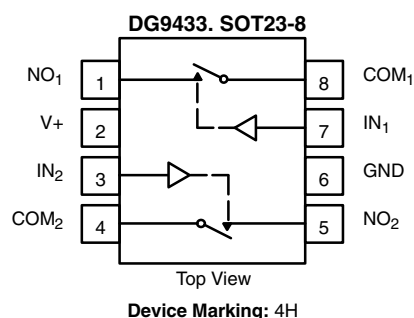
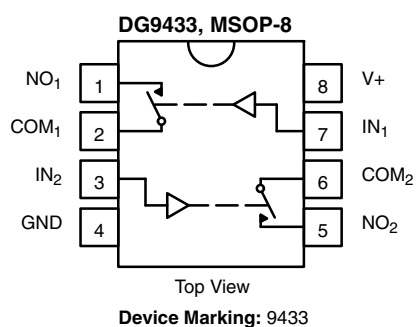
FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG9432



TRUTH TABLE DG9432

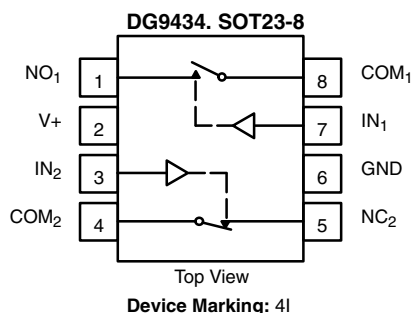
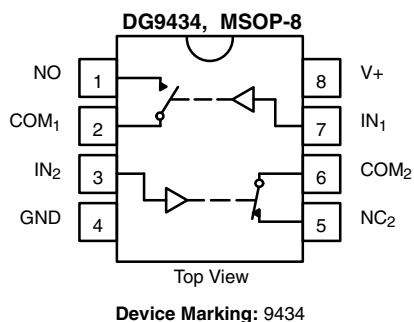
Logic	Switch
0	On
1	Off

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION - DG9433/DG9434



TRUTH TABLE DG9433

Logic	Switch
0	Off
1	On



TRUTH TABLE DG9434

Logic	Switch-1	Switch-2
0	Off	On
1	On	Off

ORDERING INFORMATION

Temp. Range	Package	Part Number
- 40 °C to 85 °C	MSOP-8	DG9432DQ-T1-E3
		DG9433DQ-T1-E3
		DG9434DQ-T1-E3
	SOT23-8	DG9432DS-T1-E3
		DG9433DS-T1-E3
		DG9433DS-T1-E3

**ABSOLUTE MAXIMUM RATINGS**

Parameter		Limit	Unit
Reference V+ to GND		- 0.3 to + 13.5	V
IN, COM, NC, NO ^a		- 0.3 to (V+ + 0.3)	
Continuous Current (Any terminal)		± 10	mA
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 20	
Storage Temperature (D suffix)		- 65 to 150	°C
Power Dissipation (Packages) ^b	MSOP-8 ^c	320	mW
	SOT23-8 ^c	515	

Notes:

a. Signals on S_X, D_X, or IN_X exceeding V+ or V- will be clamped by internal diodes. Limit forward diode current to maximum current ratings.

b. All leads welded or soldered to PC board.

c. Derate 6.5 mW/°C above 75 °C.

SPECIFICATIONS V+ = 3 V

Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 3.3 V, ± 10 %, V _{IN} = 0.4 V or 1.8 V ^e	Temp. ^a	Limits - 40 °C to 85 °C			Unit
				Min. ^c	Typ. ^b	Max. ^c	
Switch On Resistance							
Analog Signal Range ^e	V _{ANALOG}		Full	V-		V+	V
Drain-Source On- Resistance	R _(on)	V+ = 2.7 V, I _{COM} = 1 mA, V _{COM} = 1.5 V	Room Full		81	100 120	Ω
R _{ON} Match ^d	ΔR _{on}		Room		0.4	3.0	
Digital Control							
Input, High Voltage	V _{INH}	V+ Ranges 2.7 to 5 V	Full	1.8			V
Input, Low Voltage	V _{INL}		Full			0.4	
Input Current	I _{INH}			- 1		1	μA
Dynamic Characteristics							
Break-Before-Make ^{d,g}	t _{OPEN}	V+ = 3 V, R _L = 300 Ω V _{NO} = V _{NC} = 1.5 V C _L = 35 pF, V _{IN} = 0 V, 3 V	Room Full	1			ns
Turn-On Time ^d	t _{ON}		Room Full		60	80 100	
Turn-Off Time ^d	t _{OFF}		Room Full		14	25 35	
Charge Injection ^d	Q	C _L = 1 nF, R _{GEN} = 0 Ω, V _g = 0 V	Room		0.16		pC
Off-Isolation ^d	OIRR	C _L = 5 pF, R _L = 50 Ω, f = 1 MHz	Room		77		dB
		C _L = 5 pF, R _L = 50 Ω, f = 10 MHz	Room		55		
Crosstalk ^d	X _{TALK}	R _L = 50 Ω, f = 1 MHz, V+ = 2.5 V	Room		98		
Source Off Capacitance ^d	C _{NO/NC(off)}	f = 1 MHz, V _{NC/NO} = 0 V	Room		7.5		pF
Drain Off Capacitance ^d	C _{COM(off)}	f = 1 MHz V _{COM} = 0 V	Room		7.8		
Drain On Capacitance ^d	C _{COM(on)}		Room		22		
Supply Current	I+	V+ = 3.3 V, V _{IN} = 0 or V+	Room	- 1		- 1	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

d. Guarantee by design, not subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Guaranteed by 12 V leakage testing, not production tested.

g. Applies for DG9434 only.

SPECIFICATIONS V+ = 5 V							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 5 V, ± 10 %, VIN = 0.4 V or 1.8 V ^e	Temp. ^a	Limits - 40 °C to 85 °C			Unit
				Min. ^c	Typ. ^b	Max. ^c	
Switch On Resistance							
Analog Signal Range ^e	V _{ANALOG}		Full	V-		V+	V
Drain-Source On-Resistance	R _(on)	V+ = 4.5 V, I _{COM} = 1 mA V _{COM} = 2.5 V or 3.5 V	Room Full		39	60 70	Ω
R _{DS(on)} Match	ΔR _(on)	V+ = 4.5 V, I _{COM} = 1 mA, V _{COM} = 3.5 V	Room		0.3	3.0	
Switch Off Leakage Current ^f	I _{NC/NO(off)}	V+ = 5 V, V _{COM} = 0.5 V, 4.5 V V _{NC/NO} = 4.5 V, 0.5 V	Room Full	- 1 - 10	0.3	1 10	nA
	I _{COM(off)}		Room Full	- 1 - 10	0.3	1 10	
Channel On Leakage Current ^f	I _{COM(on)}		Room Full	- 1 - 10	0.3	1 10	
Digital Control							
Input, High Voltage	V _{INH}	V+ Ranges 2.7 to 5 V	Full	1.8			V
Input, Low Voltage	V _{INL}		Full			0.4	
Input Current	I _{INH}			- 1		1	μA
Dynamic Characteristics							
Break-Before-Make ^{d,g}	t _{OPEN}	V+ = 5 V, R _L = 300 Ω V _{NO} = V _{NC} = 3 V C _L = 35 pF, V _{IN} = 0 V, 5 V	Room Full	1			ns
Turn-On Time	t _{ON}		Room Full		33	60 70	
Turn-Off Time	t _{OFF}		Room Full		10	20 30	
Charge Injection ^d	Q	C _L = 1 nF, R _{GEN} = 0 Ω, V _g = 0 V	Room		0.56		pC
Off-Isolation ^d	OIRR	C _L = 5 pF, R _L = 50 Ω, f = 1 MHz	Room		76		dB
		C _L = 5 pF, R _L = 50 Ω, f = 10 MHz, V+ = 5 V	Room		54		
Crosstalk ^d	X _{TALK}	R _L = 50 Ω, f = 1 MHz, V+ = 5 V	Room		96		
Source Off Capacitance ^d	C _{NC/NO(off)}	f = 1 MHz, V _{NC/NO} = 0 V	Room		7.5		pF
Drain Off Capacitance ^d	C _{COM(off)}	f = 1 MHz, V _{COM} = 0 V	Room		7.8		
Drain On Capacitance ^d	C _{COM(on)}		Room		22		
Supply Current	I+	V+ = 5.5 V, VIN = 0 or V+	Room	- 1		- 1	μA

Notes:

a. Room = 25 °C, Full = as determined by the operating suffix.

b. Typical values are for design aid only, not guaranteed nor subject to production testing.

c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.

d. Guarantee by design, not subjected to production test.

e. V_{IN} = input voltage to perform proper function.

f. Guaranteed by 12 V leakage testing, not production tested.

g. Applies for DG9434 only.



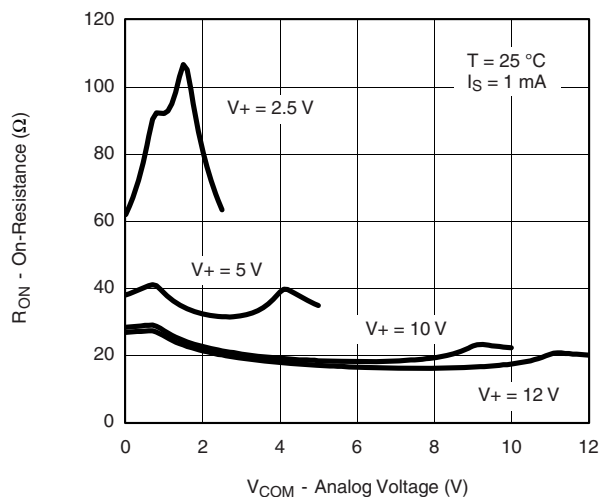
SPECIFICATIONS V+ = 12 V							
Parameter	Symbol	Test Conditions Otherwise Unless Specified V+ = 12 V, ± 10 %, VIN = 0.8 V or 2.4 V ^e	Temp. ^a	Limits - 40 °C °C to 85 °C			Unit
				Min. ^c	Typ. ^b	Max. ^c	
Switch On Resistance							
Analog Signal Range ^e	V _{ANALOG}		Full	V-		V+	V
Drain-Source On-Resistance	R _(on)	V+ = 10.8 V, I _{COM} = 1 mA, V _{COM} = 9 V	Room Full		19	30 40	Ω
R _{DS(on)} Match	ΔR _(on)		Room		0.3	3.0	
Switch Off Leakage Current ^a	I _{NC/NO(off)}	V+ = 12 V, V _S = 1/11 V, V _{COM} = 11/1 V	Room Full	- 1 - 10	0.3	1 10	nA
	I _{COM(off)}		Room Full	- 1 - 10	0.3	1 10	
Channel On Leakage Current ^a	I _{COM(on)}		Room Full	- 1 - 10	0.3	1 10	
Digital Control							
Input, High Voltage	V _{INH}	V+ = 12 V	Full			2.4	V
Input, Low Voltage	V _{INL}		Full	0.8			
Input Current	I _{INH}			- 1		1	μA
Dynamic Characteristics							
Break-Before-Make ^{d,g}	t _{OPEN}	V+ = 12 V, R _L = 300 Ω V _{NO} = V _{NC} = 8 V C _L = 35 pF, V _{IN} = 0 V, 12 V	Room Full	1			ns
Turn-On Time	t _{ON}		Room Full		21	35 40	
Turn-Off Time	t _{OFF}		Room Full		6	18 25	
Charge Injection ^d	Q	C _L = 1 nF, R _{GEN} = 0 Ω, V _g = 0 V, V+ = 5 V	Room		0.36		pC
Off-Isolation ^d	OIRR	C _L = 5 pF, R _L = 50 Ω, f = 1 MHz	Room		75		dB
		C _L = 5 pF, R _L = 50 Ω, f = 10 MHz	Room		53		
Crosstalk ^d	X _{TALK}	R _L = 50 Ω, f = 1 MHz, V+ = 5 V	Room		96		
Source Off Capacitance ^d	C _{NO/NC(off)}	f = 1 MHz, V _{NC/NO} = 0 V	Room		7.5		pF
Drain Off Capacitance ^d	C _{COM(off)}	f = 1 MHz, V _{COM} = 0 V	Room		7.8		
Drain On Capacitance ^d	C _{COM(on)}		Room		22		
Supply Current	I+	V+ = 12 V, V _{IN} = 0 or V+	Room	- 1		- 1	μA

Notes:

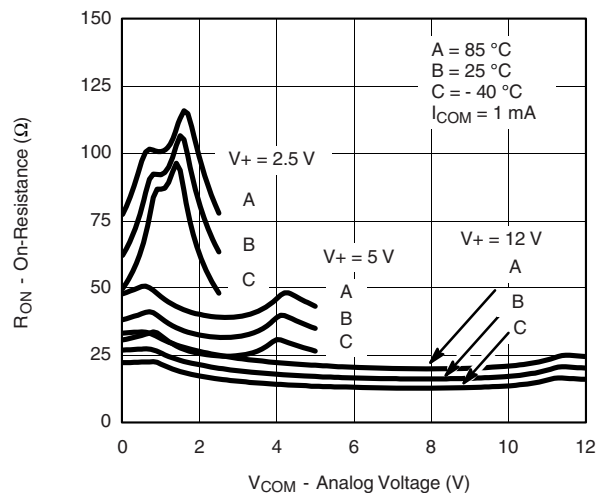
- a. Room = 25 °C, Full = as determined by the operating suffix.
b. Typical values are for design aid only, not guaranteed nor subject to production testing.
c. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this datasheet.
d. Guarantee by design, not subjected to production test.
e. V_{IN} = input voltage to perform proper function.
f. Guaranteed by 12 V leakage testing, not production tested.
g. Applies for DG9434 only.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

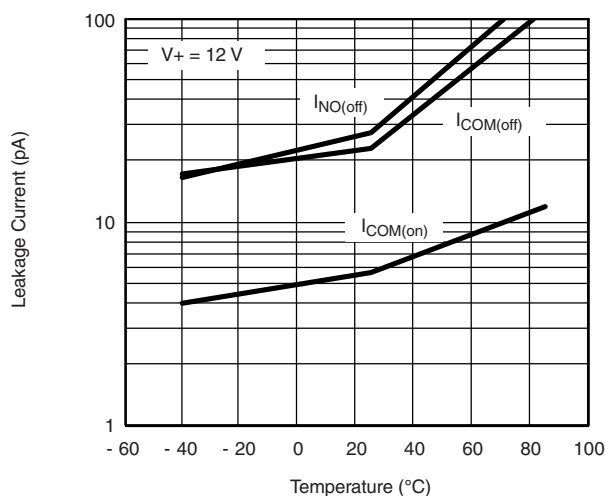
TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



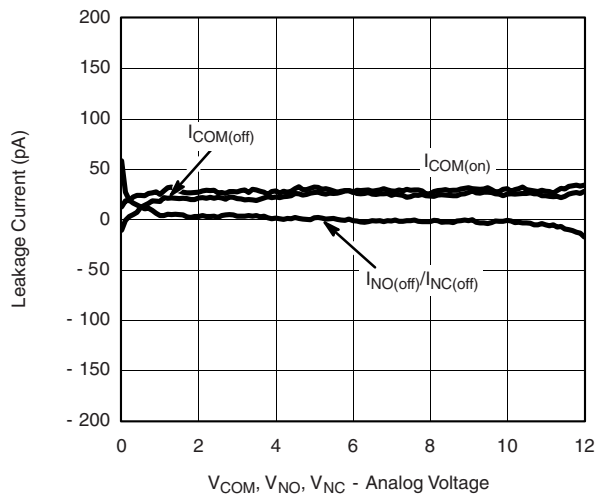
R_{ON} vs. V_{COM} and Single Supply Voltage



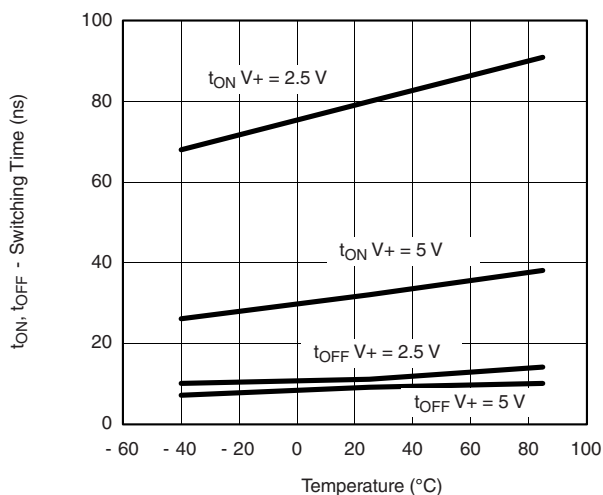
R_{ON} vs. Analog Voltage and Temperature



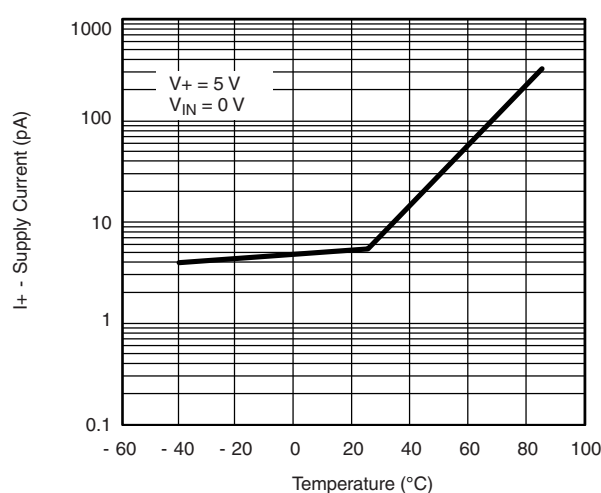
Leakage Current vs. Temperature



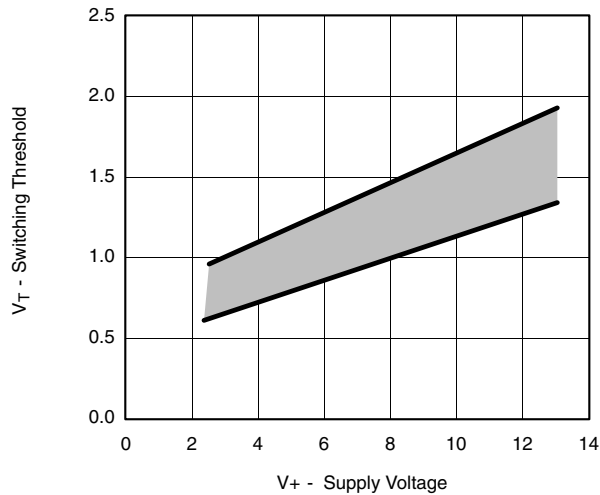
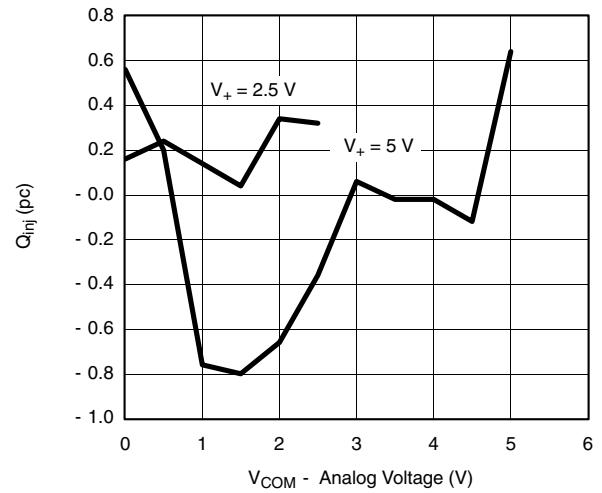
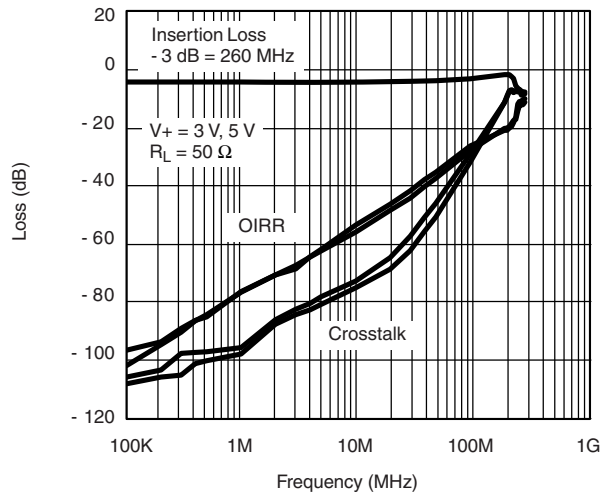
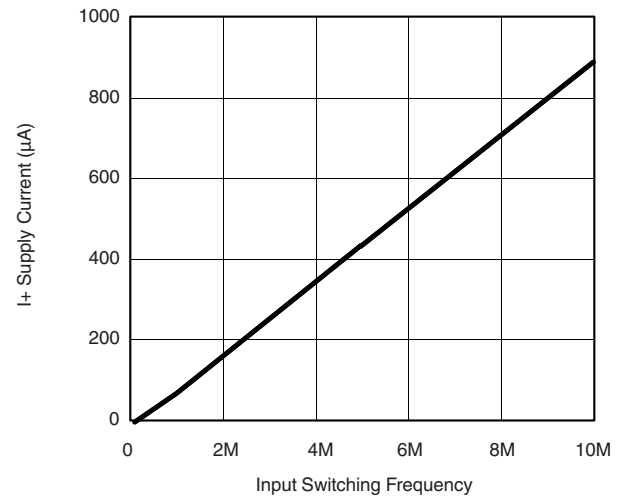
Leakage Current vs. Analog Voltage



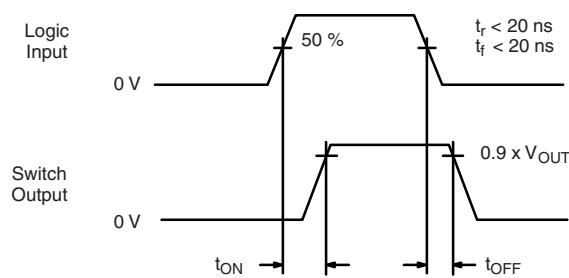
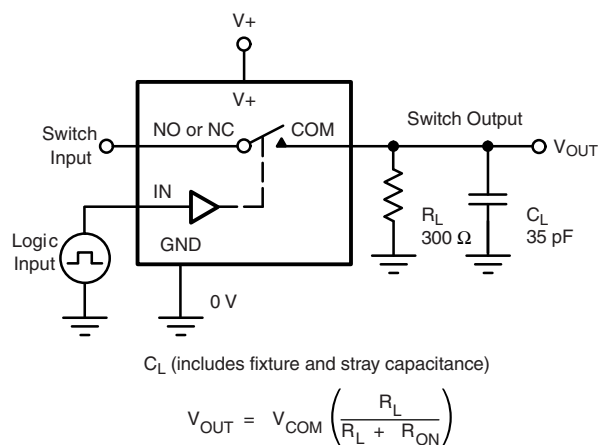
Switching Time vs. Temperature



Supply Current vs. Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Switching Threshold vs. Supply Voltage

Charge Injection at Source

Insertion Loss, Off Isolation and Crosstalk vs. Frequency

Supply Current vs. Input Switching Frequency

TEST CIRCUITS



Logic "1" = Switch On
Logic input waveforms inverted for switches that have the opposite logic sense.

Figure 1. Switching Time

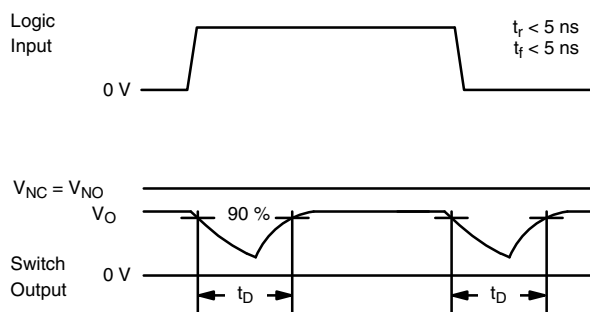
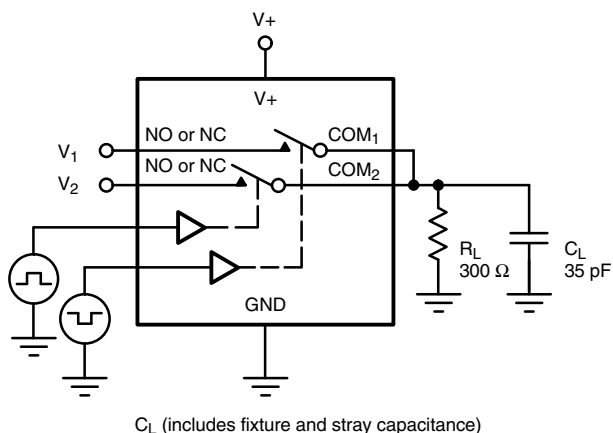
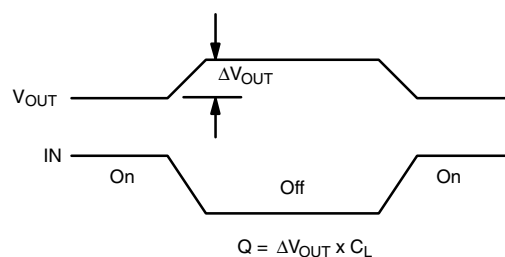
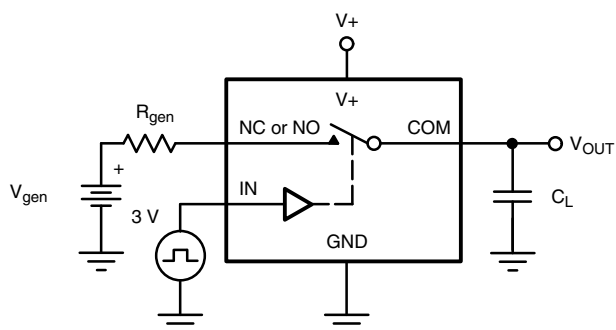


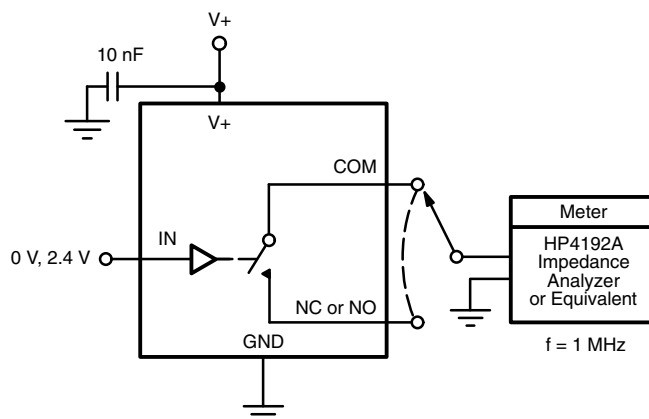
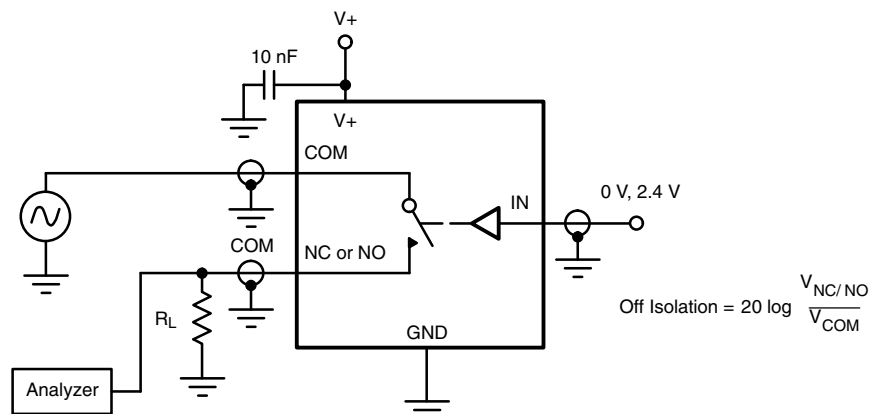
Figure 2. Break-Before-Make Interval



IN depends on switch configuration: input polarity determined by sense of switch.

Figure 3. Charge Injection

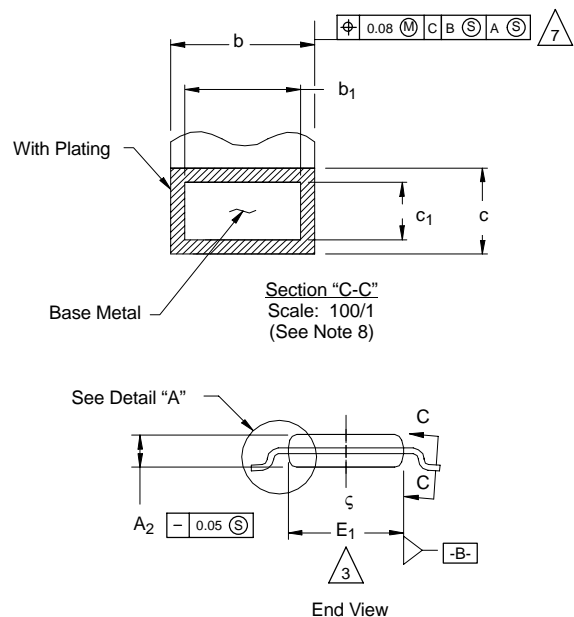
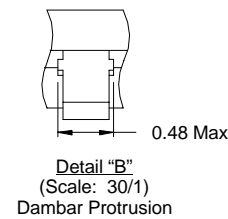
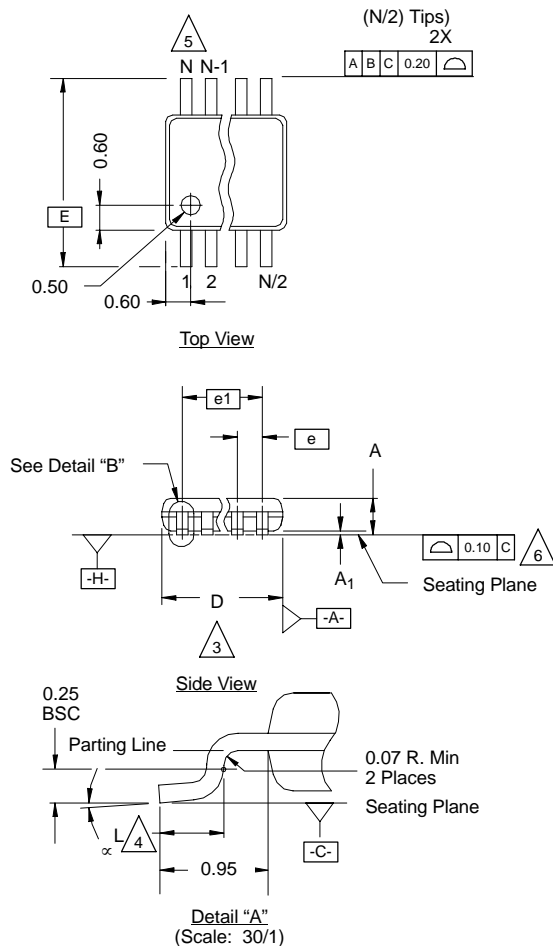
TEST CIRCUITS



Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?72311.

MSOP: 8-LEADS

JEDEC Part Number: MO-187, (Variation AA and BA)



NOTES:

1. Die thickness allowable is 0.203 ± 0.0127 .
2. Dimensioning and tolerances per ANSI.Y14.5M-1994.
3. Dimensions "D" and "E₁" do not include mold flash or protrusions, and are measured at Datum plane **[-H-]**, mold flash or protrusions shall not exceed 0.15 mm per side.
4. Dimension is the length of terminal for soldering to a substrate.
5. Terminal positions are shown for reference only.
6. Formed leads shall be planar with respect to one another within 0.10 mm at seating plane.
7. The lead width dimension does not include Dambar protrusion. Allowable Dambar protrusion shall be 0.08 mm total in excess of the lead width dimension at maximum material condition. Dambar cannot be located on the lower radius or the lead foot. Minimum space between protrusions and an adjacent lead to be 0.14 mm. See detail "B" and Section "C-C".
8. Section "C-C" to be determined at 0.10 mm to 0.25 mm from the lead tip.
9. Controlling dimension: millimeters.
10. This part is compliant with JEDEC registration MO-187, variation AA and BA.
11. Datums **[-A-]** and **[-B-]** to be determined Datum plane **[-H-]**.
12. Exposed pad area in bottom side is the same as the leadframe pad size.

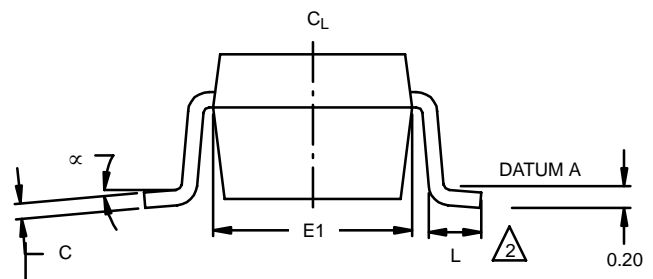
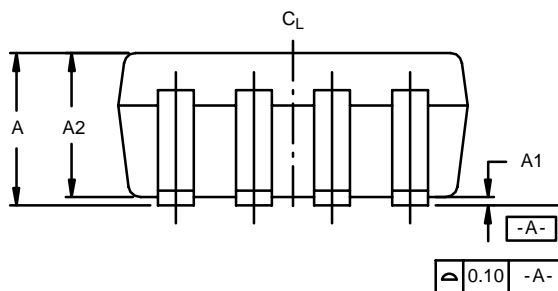
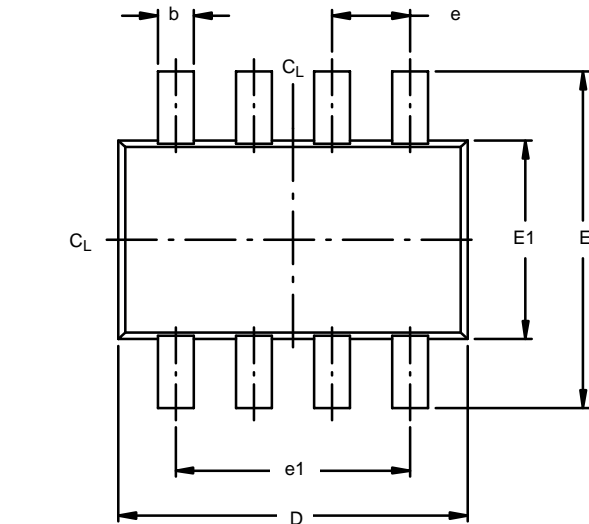
N = 8L

Dim	MILLIMETERS			Note
	Min	Nom	Max	
A	-	-	1.10	
A₁	0.05	0.10	0.15	
A₂	0.75	0.85	0.95	
b	0.25	-	0.38	8
b₁	0.25	0.30	0.33	8
c	0.13	-	0.23	
c₁	0.13	0.15	0.18	
D	3.00 BSC			3
E	4.90 BSC			
E₁	2.90	3.00	3.10	3
e	0.65 BSC			
e₁	1.95 BSC			
L	0.40	0.55	0.70	4
N	8			5
α	0°	4°	6°	

ECN: T-02080—Rev. C, 15-Jul-02
DWG: 5867



SOT-23 : 8-LEAD



NOTES:

1. All dimensions are in millimeters.
2. Foot length measured at intercept point between Datum A and lead surface.
3. Package outline exclusive of mold flash and metal burr.
4. Package outline inclusive of solder plating.
5. No molding flash allowed on the top and bottom lead surface.

Dim	MILLIMETERS			INCHES		
	Min	Nom	Max	Min	Nom	Max
A	0.90	1.27	1.45	0.035	0.05	0.057
A1	0.00	0.0762	0.15	0.000	0.003	0.006
A2	0.90	1.20	1.30	0.035	0.047	0.051
b	0.22	0.30	0.38	0.009	0.012	0.015
C	0.09	0.152	0.20	0.004	0.006	0.008
D	2.80	2.9	3.00	0.11	0.114	0.118
E	2.60	2.8	23.00	0.102	0.11	0.118
E1	1.50	1.65	1.75	0.059	0.065	0.069
e	0.65 REF			0.026 REF		
e1	1.95 REF			0.077 REF		
L	0.35	0.45	0.55	0.014	0.018	0.022
α	0°	4°	8°	0°	4°	8°
ECN: C-03085—Rev. A, 07-Apr-03 DWG: 5895						



Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk and agree to fully indemnify and hold Vishay and its distributors harmless from and against any and all claims, liabilities, expenses and damages arising or resulting in connection with such use or sale, including attorneys fees, even if such claim alleges that Vishay or its distributor was negligent regarding the design or manufacture of the part. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.